## High Current Surface Mount <br> NPN Silicon Switching <br> Transistor for Load <br> Management in Portable Applications

## Features

- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right)$

| Rating | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Emitter Voltage | $\mathrm{V}_{\mathrm{CEO}}$ | 30 | Vdc |
| Collector-Base Voltage | $\mathrm{V}_{\mathrm{CBO}}$ | 50 | Vdc |
| Emitter-Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 5.0 | Vdc |
| Collector Current - Continuous | $\mathrm{I}_{\mathrm{C}}$ | 1.0 | A |
| Collector Current - Peak | $\mathrm{I}_{\mathrm{CM}}$ | 2.0 | A |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :---: | :---: | :---: | :---: |
| Total Device Dissipation (Note 1) $@ \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ | $P_{D}$ | $\begin{aligned} & 310 \\ & 2.5 \end{aligned}$ | $\begin{gathered} \mathrm{mW} \\ \mathrm{~mW} /{ }^{\circ} \mathrm{C} \end{gathered}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 403 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Total Device Dissipation (Note 2) $@ T_{A}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ | $P_{D}$ | $\begin{gathered} 710 \\ 5.7 \end{gathered}$ | $\begin{gathered} \mathrm{mW} \\ \mathrm{~mW} /{ }^{\circ} \mathrm{C} \end{gathered}$ |
| Thermal Resistance, Junction-to-Ambient (Note 2) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 176 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Total Device Dissipation (Single Pulse < 10 s) | P ${ }_{\text {Dsingle }}$ | 575 | mW |
| Junction and Storage Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ Minimum Pad
2. FR-4@ $1.0 \times 1.0$ inch Pad

ON Semiconductor ${ }^{\circledR}$
http://onsemi.com
30 VOLTS, 2.0 AMPERES
NPN TRANSISTOR


MARKING DIAGRAM


N3 = Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| MMBT489LT1G | SOT-23 <br> (Pb-Free) | 3000/Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |
| $\begin{aligned} & \text { Collector-Emitter Breakdown Voltage } \\ & \quad\left(I_{C}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right) \end{aligned}$ | $\mathrm{V}_{\text {(BR)CEO }}$ | 30 | - | Vdc |
| Collector-Base Breakdown Voltage $\left(\mathrm{I}_{\mathrm{C}}=0.1 \mathrm{mAdc}, \mathrm{I}_{\mathrm{E}}=0\right)$ | $\mathrm{V}_{\text {(BR) }{ }^{\text {CBO }}}$ | 50 | - | Vdc |
| Emitter-Base Breakdown Voltage $\left(\mathrm{I}_{\mathrm{E}}=0.1 \mathrm{mAdc}, \mathrm{I}_{\mathrm{C}}=0\right)$ | $\mathrm{V}_{\text {(BR) }{ }^{\text {Ebo }}}$ | 5.0 | - | Vdc |
| Collector Cutoff Current $\left(\mathrm{V}_{\mathrm{CB}}=30 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0\right)$ | $\mathrm{I}_{\text {cbo }}$ | - | 0.1 | $\mu \mathrm{Adc}$ |
| $\begin{aligned} & \text { Collector-Emitter Cutoff Current } \\ & \left(V_{\text {CES }}=30 \mathrm{Vdc}\right) \end{aligned}$ | $I_{\text {CES }}$ | - | 0.1 | $\mu \mathrm{Adc}$ |
| Emitter Cutoff Current $\left(\mathrm{V}_{\mathrm{EB}}=4.0 \mathrm{Vdc}\right)$ | ${ }_{\text {E }}$ ebo | - | 0.1 | $\mu \mathrm{Adc}$ |

## ON CHARACTERISTICS

| $\begin{gathered} \text { DC Current Gain (Note 3) } \\ \left(\mathrm{I}_{\mathrm{C}}=50 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}\right) \\ \left(\mathrm{I}_{\mathrm{C}}=0.5 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}\right) \\ \left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}\right) \end{gathered}$ | $h_{\text {FE }}$ | $\begin{aligned} & 300 \\ & 300 \\ & 200 \end{aligned}$ | $9{ }_{-}^{-}$ |  |
| :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Collector-Emitter Saturation Voltage (Note 3) } \\ & \left(I_{C}=1.0 \mathrm{~A}, I_{\mathrm{B}}=100 \mathrm{~mA}\right) \\ & \left(I_{C}=0.5 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=50 \mathrm{~mA}\right) \\ & \left(I_{C}=0.1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{~mA}\right) \end{aligned}$ | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | - | $\begin{aligned} & 0.200 \\ & 0.125 \\ & 0.075 \end{aligned}$ | V |
| Base-Emitter Saturation Voltage (Note 3) $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=0.1 \mathrm{~A}\right)$ | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ | - | 1.1 | V |
| Base-Emitter Turn-on Voltage (Note 3) $\left(I_{C}=1.0 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=2.0 \mathrm{~V}\right)$ | $\mathrm{V}_{\mathrm{BE} \text { (on) }}$ | - | 1.1 | V |
| Cutoff Frequency $\left(\mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}, \mathrm{f}=100 \mathrm{MHz}\right.$ | $\mathrm{f}_{\text {T }}$ | 100 | - | MHz |
| Output Capacitance $(\mathrm{f}=1.0 \mathrm{MHz})$ | $\mathrm{C}_{\text {obo }}$ | - | 15 | pF |

3. Pulsed Condition: Pulse Width $=300 \mu \mathrm{sec}$, Duty Cycle $\leq 2 \%$


Figure 1. $\mathrm{V}_{\mathrm{CE}}$ versus $\mathrm{I}_{\mathrm{b}}$


Figure 2. $\mathrm{V}_{\mathrm{CE}}$ versus $\mathrm{I}_{\mathrm{C}}$

## MMBT489LT1G



Figure 3. $\mathrm{h}_{\mathrm{FE}}$ versus $\mathrm{I}_{\mathrm{c}}$

$\mathrm{I}_{\mathrm{c}}(\mathrm{A})$
Figure 5. $\mathrm{V}_{\mathrm{BE}(\text { sat })}$ versus $\mathrm{I}_{\mathrm{c}}$


Figure 4. $\mathrm{V}_{\mathrm{BE}(\mathrm{on})}$ versus $\mathrm{I}_{\mathrm{c}}$


Figure 6. Safe Operating Area


Figure 7. Normalized Thermal Response

## MMBT489LT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD

FINISH THICKNESS. MINIMUM LEAD
THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.040 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.018 | 0.020 |
| c | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.081 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## PUBLICATION ORDERING INFORMATION

## LITERATURE FULFILLMENT:

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